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5. (Amended) The semiconductor structure of Claim 1 wherein the dopant concentration of the first semiconductor region is greater than  $1 \times 10^{20}/\text{cm}^3$ .

6. (Amended) The semiconductor structure of Claim 1 or 5 wherein the first semiconductor region is doped primarily with boron.

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8. (Amended) The semiconductor structure of Claim 1 or 7 wherein the semiconductor structure comprises a 3-D memory array.

## REMARKS

### I. Amendment to the Specification

In this Amendment, Applicants have amended the specification to insert a serial number for a patent application formerly identified by attorney docket number.

### II. 35 U.S.C. § 112, Second Paragraph, Rejections

In the Office Action, Claims 2-6 and 8 were rejected under 35 U.S.C. § 112, second paragraph, as being indefinite for using the term "invention." In response to this rejection, Applicants have replaced the term "invention" with the term "semiconductor structure." In view of these amendments, Applicants submit that the 35 U.S.C. § 112, second paragraph, rejections have been overcome.

### III. 35 U.S.C. § 103(a) Rejections

Claims 1-8 were rejected as being unpatentable under 35 U.S.C. § 103(a) in view of the proposed combination of published U.S. patent application no. US 2002/0045342 to Hu et al. and